Stephen Hall

List of Publications by Year
in descending order

		1163117	996975
19 papers	352 citations	8 h-index	15 g-index
20 all docs	20 docs citations	20 times ranked	508 citing authors

#	Article	IF	Citations
1	Dispersion relation data for methylammonium lead triiodide perovskite deposited on a (100) silicon wafer using a two-step vapour-phase reaction process. Data in Brief, 2015, 5, 926-928.	1.0	72
2	Potassium and sodium microdomains in thin astroglial processes: A computational model study. PLoS Computational Biology, 2018, 14, e1006151.	3.2	52
3	A Reconfigurable and Biologically Inspired Paradigm for Computation Using Network-On-Chip and Spiking Neural Networks. International Journal of Reconfigurable Computing, 2009, 2009, 1-13.	0.2	46
4	Stress-Induced Positive Charge in Hf-Based Gate Dielectrics: Impact on Device Performance and a Framework for the Defect. IEEE Transactions on Electron Devices, 2008, 55, 1647-1656.	3.0	44
5	Effect of Annealing Temperature for Ni/AlOx/Pt RRAM Devices Fabricated with Solution-Based Dielectric. Micromachines, 2019, 10, 446.	2.9	33
6	The Over-Reset Phenomenon in Ta_2O_5 RRAM Device Investigated by the RTN-Based Defect Probing Technique. IEEE Electron Device Letters, 2018, 39, 955-958.	3.9	18
7	Direct Observation of Anomalous Positive Charge and Electron-Trapping Dynamics in High-k Films Using Pulsed-MOS-Capacitor Measurements. IEEE Transactions on Electron Devices, 2007, 54, 272-278.	3.0	17
8	Calcium Microdomain Formation at the Perisynaptic Cradle Due to NCX Reversal: A Computational Study. Frontiers in Cellular Neuroscience, 2019, 13, 185.	3.7	16
9	A programmable facilitating synapse device. , 2008, , .		8
10	Schottky Diodes on ZnO Thin Films Grown by Plasma-Enhanced Atomic Layer Deposition. IEEE Transactions on Electron Devices, 2017, 64, 1225-1230.	3.0	8
11	Oxides for Rectenna Technology. Materials, 2021, 14, 5218.	2.9	8
12	Failure Analysis of Power Silicon Devices at Operation above 200ï¿½C Junction Temperature. , 2007, , .		7
13	Plasma of Arc Discharge in Water for the Formation of Diverse Nanostructures Dependent on the Anode Material. IEEE Transactions on Plasma Science, 2011, 39, 2628-2629.	1.3	5
14	A high speed PE-ALD ZnO Schottky diode rectifier with low interface-state density. Journal Physics D: Applied Physics, 2018, 51, 065102.	2.8	5
15	A Biologically Plausible Neuron Circuit. Neural Networks (IJCNN), International Joint Conference on, 2007, , .	0.0	4
16	Bound states within the notch of the HfO2/GeO2/Ge stack. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	1.2	4
17	Analysis of electron capture at oxide traps by electric field injection. Applied Physics Letters, 2013, 102, .	3.3	3
18	Internal photoemission technique for high-k oxide/semiconductor band offset determination: The influence of semiconductor bulk properties. , 2014, , .		2

#	ARTICLE	IF	CITATIONS
19	A Solid State Neuron for the Realisation of Highly Scaleable Third Generation Neural Networks. , 2006, , .		0